

Abstract

Methods and systems for fabricating integrated pairs of HBT/FET's are disclosed. One preferred embodiment comprises a method of fabricating an integrated pair of GaAs-based HBT and FET. The method comprises the steps of: growing a first set of epitaxial layers for fabricating the FET on a semi-insulating GaAs substrate; fabricating a highly doped thick GaAs layer serving as the cap layer for the FET and the subcollector layer for the HBT; and producing a second set of epitaxial layers for fabricating the HBT.